

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/716,249 on August 12, 2005

Combined Classifications

12	257/E21.651
10	257/301
10	257/E27.092
8	257/E27.094
7	257/296
7	257/305
5	257/304
5	257/E21.648
5	438/392
4	257/303
4	257/311
4	257/E21.008
4	257/E27.089
4	438/243
4	438/244
4	438/249
3	257/306
3	257/465
3	257/466
3	257/E21.646
3	257/E27.096
3	365/149
3	438/242
3	438/386
2	257/300
2	257/307
2	257/382
2	257/448
2	257/461
2	257/462
2	257/618
2	257/E21.143
2	257/E21.151
2	257/E21.396
2	257/E21.538
2	257/E21.645
2	257/E21.65
2	257/E21.652
2	257/E21.653
2	257/E27.086
2	257/E27.093
2	257/E27.095
2	257/E27.112
2	257/E27.131
2	257/E27.133
2	257/E29.262
2	257/E29.267
2	365/182
2	438/152
2	438/239
2	438/254
2	438/259
2	438/270
2	438/302
2	438/387
2	438/388
2	438/389
2	438/73
2	438/977

Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/716,249 on August 12, 2005

10 257/301 (6 OR, 4 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/264 ...Enhancement mode or with high resistivity
 channel (e.g., doping of 10^{15} cm⁻³ or less)
 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
 257/296 ..Insulated gate capacitor or insulated gate
 transistor combined with capacitor (e.g., dynamic memory
 cell)
 257/301 ...Capacitor in trench

7 257/296 (3 OR, 4 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/264 ...Enhancement mode or with high resistivity
 channel (e.g., doping of 10^{15} cm⁻³ or less)
 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
 257/296 ..Insulated gate capacitor or insulated gate
 transistor combined with capacitor (e.g., dynamic memory
 cell)

7 257/305 (2 OR, 5 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/264 ...Enhancement mode or with high resistivity
 channel (e.g., doping of 10^{15} cm⁻³ or less)
 257/288 .Having insulated electrode (e.g., MOSFET, MOS
 diode)
 257/296 ..Insulated gate capacitor or insulated gate
 transistor combined with capacitor (e.g., dynamic
 memory cell)
 257/301 ...Capacitor in trench
 257/305With means to insulate adjacent storage
 nodes (e.g., channel stops or field oxide)

5 257/304 (2 OR, 3 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/264 ...Enhancement mode or with high resistivity
 channel (e.g., doping of 10^{15} cm⁻³ or less)
 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
 257/296 ..Insulated gate capacitor or insulated gate
 transistor combined with capacitor (e.g., dynamic
 memory cell)
 257/301 ...Capacitor in trench
 257/304Storage node isolated by dielectric from
 semiconductor substrate

5 438/392 (1 OR, 4 XR)
 Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
 438/381 MAKING PASSIVE DEVICE (E.G., RESISTOR,CAPACITOR, ETC.)
 438/386 .Trench capacitor
 438/389 ..Including doping of trench surfaces
 438/392 ...Doping by outdiffusion from a dopant source layer (e.g.,
 doped oxide)

PLUS Search Results for S/N 10/716,249, Searched August 12, 2005

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

5371032	5521111	5187550	6107153	5466636
5414285	4988637	5217918	6121651	5498564
5330936	5223730	5234854	4797373	5543348
6232626	5234856	5262662	4833094	5563433
6500692	6249017	5321285	4958206	5627092
6611037	5026659	5702969	5185292	5670805
6730980	5386131	5732014	5225697	5824582
6767759	4954854	5753549	5309008	5885863
6838742	4967248	5897351	5411905	5892707
5198995	5021355	5900659	5448090	5937296